L Number	Hits	Search Text	DB	Time stamp
-	26	(pix I and TFT and display and driver and	USPAT;	2003/01/29
		substrate and gat and lectr de and	US-PGPUB;	10:49
;		(chann I r (channel n ar f rming) r	EPO; JPO;	
		channel-forming)).clm.	DERWENT;	
	•	- //	IBM_TDB	
	612	(pixel near TFT).ti,ab,clm.	USPAT;	2003/01/29
			US-PGPUB;	10:51
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	23	((pixel near TFT).ti,ab,clm.) and (driver	USPAT;	2003/01/29
		near5 TFT).clm.	US-PGPUB;	10:53
		110410 11 1/1011111	EPO; JPO;	10.00
			DERWENT;	
			IBM_TDB	
	26696	(tft or (thin near film near transistor)).ab.	USPAT;	2003/01/29
	20000	(tre or (thin hear thin hear transfering)	US-PGPUB;	10:55
			EPO; JPO;	10.00
1			DERWENT;	
			IBM_TDB	
	2959	((tft or (thin near film near transistor)).ab.)	USPAT;	2003/01/29
	2939		US-PGPUB;	10:56
		and (tft or (thin near film near	,	10:50
		transistor)).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	1332	(((tft or (thin near film near transistor)).ab.)	USPAT;	2003/01/29
		and (tft or (thin near film near	US-PGPUB;	10:56
		transistor)).clm.) and (pixel).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
·	869	((((tft or (thin near film near transistor)).ab.)	USPAT;	2003/01/29
		and (tft or (thin near film near	US-PGPUB;	10:56
		transistor)).clm.) and (pixel).clm.) and	EPO; JPO;	
		(pixel).ab.	DERWENT;	
			IBM_TDB	
'	684	(((((tft or (thin near film near transistor)).ab.)	USPAT;	2003/01/29
		and (tft or (thin near film near	US-PGPUB;	10:57
		transistor)).clm.) and (pixel).clm.) and	EPO; JPO;	
		(pixel).ab.) and gate.clm.	DERWENT;	
			IBM_TDB	
•	653	((((((tft or (thin near film near	USPAT;	2003/01/29
		transistor)).ab.) and (tft or (thin near film	US-PGPUB;	10:57
		near transistor)).clm.) and (pixel).clm.) and	EPO; JPO;	
		(pixel).ab.) and gate.clm.) and	DERWENT;	
		electrode.clm.	IBM_TDB	
	75	((((((tft or (thin near film near	USPAT;	2003/01/29
		transist r)).ab.) and (tft r (thin near film	US-PGPUB;	10:57
		near transist r)).clm.) and (pix l).clm.) and	EPO; JPO;	
		(pix I).ab.) and gate.clm.) and	DERWENT;	1
		I ctr de.clm.) and driv r.clm.	IBM_TDB	

•	189	((((((tft r (thin near film n ar	USPAT;	2003/01/29
		transist r)).ab.) and (tft r (thin near film	US-PGPUB;	10:57
		n ar transist r)).clm.) and (pix l).clm.) and	EPO; JP ;	
		(pix I).ab.) and gate.clm.) and	DERWENT;	
		el ctrod .clm.) and driv r	IBM_TDB	ł
	581	(((((((tft or (thin near film near	USPAT;	2003/01/29
		transist r)).ab.) and (tft or (thin n ar film	US-PGPUB;	10:58
		near transistor)).clm.) and (pixel).clm.) and	EPO; JPO;	
		(pixel).ab.) and gate.clm.) and	DERWENT;	
		electrode.clm.) and (display or displaying or	IBM_TDB	
	i	displayed).ti,ab,clm.		İ
	413	(((((((tft or (thin near film near	USPAT;	2003/01/29
		transistor)).ab.) and (tft or (thin near film	US-PGPUB;	10:59
		near transistor)).clm.) and (pixel).clm.) and	EPO; JPO;	
		(pixel).ab.) and gate.clm.) and	DERWENT;	
		electrode.clm.) and (display or displaying or	IBM_TDB	
		displayed).ti,ab,clm.) and (channel or		
	;	(channel near forming) or channel-forming)		
	105	((((((((tft or (thin near film near	USPAT;	2003/01/29
		transistor)).ab.) and (tft or (thin near film	US-PGPUB;	11:00
		near transistor)).clm.) and (pixel).clm.) and	EPO; JPO;	
		(pixel).ab.) and gate.clm.) and	DERWENT;	
		electrode.clm.) and (display or displaying or	IBM_TDB	
		displayed).ti,ab,clm.) and (channel or		
		(channel near forming) or channel-forming))		
		and capacitor.clm.		

L Number	Hits	Search Text	DB	Tim stamp
• umber	1442	(((display r displaying r display d r pix l) near20 (substrat) n ar20 driv r)) and (tft or (thin n ar film near transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 11:18
-	668	(((display or displaying or displayed or pixel) near20 (substrate) near20 driver)) and (tft or (thin near film near transistor)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 11:19
-	573	((((display or displaying or displayed or pixel) near20 (substrate) near20 driver)) and (tft or (thin near film near transistor)).clm.) and (lcd or display or (liquid near crystal)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 11:20
-	559	(((((display or displaying or displayed or pixel) near20 (substrate) near20 driver)) and (tft or (thin near film near transistor)).clm.) and (lcd or display or (liquid near crystal)).ti,ab,clm.) and (display or displaying or displayed).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 11:20
	281	((((((display or displaying or displayed or pixel) near20 (substrate) near20 driver)) and (tft or (thin near film near transistor)).clm.) and (lcd or display or (liquid near crystal)).ti,ab,clm.) and (display or displaying or displayed).ti,ab,clm.) and (substrate).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 11:20
	244	(((((((display or displaying or displayed or pixel) near20 (substrate) near20 driver)) and (tft or (thin near film near transistor)).clm.) and (lcd or display or (liquid near crystal)).ti,ab,clm.) and (display or displaying or displayed).ti,ab,clm.) and (substrate).ab.) and (channel or (channel near forming))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 11:21
-	217	((((((((((((((((((((((((((((((((((((((USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 11:22

-	67	(((((((display or displaying r display d r	USPAT;	2003/01/29
		pix I) n ar20 (substrat) near20 driver)) and (tft r (thin near film n ar transist r)). Im.)	US-PGPUB; EPO; JPO;	11:22
	1	and (lcd r display r (liquid n ar	DERWENT;	
	İ	crystal)).ti,ab,clm.) and (display r	IBM_TDB	
		displaying r display d).ti,ab,clm.) and		!
		(substrat).ab.) and (chann I or (channel		
		near forming))) and ((display or displaying or		
	ļ	displayed or pixel) near10 (substrate)		
		near10 driver).ti.ab.clm.		

L Number	Hits	Search Text	DB	Time stamp
- Number	20	((pix I n ar100 (drive or driv r) near100 (tft	USPAT;	2003/01/29
		r (thin n ar film n ar transist r))) near100	US-PGPUB;	16:39
		gate near100 ctrode near100 (conducting	EPO; JPO;	
		rc nductiv rm tal or conductor or	DERWENT;	
		layer)).clm.	IBM_TDB	
•	18	(((pixel near100 (drive or driver) near100 (tft	USPAT;	2003/01/29
		or (thin near film near transistor))) near100	US-PGPUB;	16:37
		gate near100 electrode near100 (conducting	EPO; JPO;	
		or conductive or metal or conductor or	DERWENT;	
		layer)).clm.) and (size or dense or density or	IBM_TDB	
	1	densely)	_	
-	18	(((pixel near100 (drive or driver) near100 (tft	USPAT;	2003/01/29
		or (thin near film near transistor))) near100	US-PGPUB;	16:38
		gate near100 electrode near100 (conducting	EPO; JPO;	
		or conductive or metal or conductor or	DERWENT;	
		layer)).clm.) and (size or dense or density or	IBM_TDB	
		densely or compact or packed)		
_	2	(((pixel near100 (drive or driver) near100 (tft	USPAT;	2003/01/29
	_	or (thin near film near transistor))) near100	US-PGPUB;	16:38
		gate near100 electrode near100 (conducting	EPO; JPO;	
		or conductive or metal or conductor or	DERWENT;	
		layer)).clm.) and (size or dense or density or	IBM_TDB	
		densely or compact or packed).ti,ab,clm.		
_	5	((pixel near100 (drive or driver) near100 (tft	USPAT;	2003/01/29
-		or (thin near film near transistor))) near100	US-PGPUB;	16:41
		gate near100 electrode near100 (conducting	EPO; JPO;	10.41
		or conductive or metal or conductor or	DERWENT;	
		layer) near100 (substrate) near100 (channel	IBM_TDB	
		or channel-forming)).clm.		
_	5	((pixel near200 (drive or driver) near200 (tft	USPAT;	2003/01/29
_		or (thin near film near transistor))) near200	US-PGPUB;	16:44
		gate near200 electrode near200 (conducting	EPO; JPO;	
		or conductive or metal or conductor or	DERWENT;	
		layer) near200 (substrate) near200 (channel	IBM TDB	
		or channel-forming)).clm.		
	8	((pixel near200 (drive or driver) near200 (tft	USPAT;	2003/01/31
		or (thin near film near transistor))) near200	US-PGPUB;	13:40
		gate near200 electrode near200 (conducting	EPO; JPO;	
		or conductive or metal or conductor or	DERWENT;	
		layer) near200 (substrate) near200 (channel	IBM_TDB	
		or channel-forming)).ti,ab,clm.		
-	126674	pixel.ti,ab,clm.	USPAT;	2003/01/31
	1.20074	F	US-PGPUB;	13:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	9544	pixel.ti,ab,clm. and (tft or (thin n ar film	USPAT;	2003/01/31
	3344	near transist r)).ti,ab,clm.	US-PGPUB;	13:51
			EPO; JPO;	
			DERWENT;	
	ļ		IBM_TDB	

•	2055	(pix l.ti,ab,clm. and (tft r (thin n ar film	USPAT;	2003/01/31
		near transist r)).ti,ab,clm.) and (driver or	US-PGPUB;	13:49
		drive).ti,ab,clm.	EPO; JPO;	
			DERWENT;	:
			IBM_TDB	
-	864	((pix 1.ti,ab,clm. and (tft or (thin n ar film	USPAT;	2003/01/31
		n ar transist r)).ti,ab,clm.) and (driv r r	US-PGPUB;	13:50
		drive).ti,ab,clm.) and (gate and	EPO; JPO;	
		electrode).ti,ab,clm.	DERWENT;	
			IBM_TDB	
_	274	(((pixel.ti,ab,clm. and (tft or (thin near film	USPAT;	2003/01/31
		near transistor)).ti,ab,clm.) and (driver or	US-PGPUB;	13:50
		drive).ti,ab,clm.) and (gate and	EPO; JPO;	
		electrode).ti,ab,clm.) and	DERWENT;	
		1	IBM_TDB	
	94	(channel).ti,ab,clm.	USPAT;	2003/01/31
•	94	((((pixel.ti,ab,clm. and (tft or (thin near film	1	13:50
		near transistor)).ti,ab,clm.) and (driver or	US-PGPUB;	13:50
		drive).ti,ab,clm.) and (gate and	EPO; JPO;	
		electrode).ti,ab,clm.) and	DERWENT;	
		(channel).ti,ab,clm.) and (source and drain	IBM_TDB	
		and (dope or doped or doping or impurity or		
	_	dopant)).ti,ab,clm.		
•	74	(((((pixel.ti,ab,clm. and (tft or (thin near film	USPAT;	2003/01/31
		near transistor)).ti,ab,clm.) and (driver or	US-PGPUB;	13:51
		drive).ti,ab,clm.) and (gate and	EPO; JPO;	
		electrode).ti,ab,clm.) and	DERWENT;	
		(channel).ti,ab,clm.) and (source and drain	IBM_TDB	
		and (dope or doped or doping or impurity or		
		dopant)).ti,ab,clm.) and (tft or (thin near film		
		near transistor)).ab.		
-	62	((((((pixel.ti,ab,clm. and (tft or (thin near film	USPAT;	2003/01/31
		near transistor)).ti,ab,clm.) and (driver or	US-PGPUB;	13:52
		drive).ti,ab,clm.) and (gate and	EPO; JPO;	
		electrode).ti,ab,clm.) and	DERWENT;	
		(channel).ti,ab,clm.) and (source and drain	IBM_TDB	
		and (dope or doped or doping or impurity or	1	
		dopant)).ti,ab,clm.) and (tft or (thin near film		
		near transistor)).ab.) and (display or		:
		displaying or displayed).ti,ab,clm.		
•	45	(((((((pixel.ti,ab,clm. and (tft or (thin near	USPAT;	2003/01/31
		film near transistor)).ti,ab,clm.) and (driver	US-PGPUB;	13:53
•		or drive).ti,ab,clm.) and (gate and	EPO; JPO;	
		electrode).ti,ab,clm.) and	DERWENT;	
		(channel).ti,ab,clm.) and (source and drain	IBM_TDB	
		and (dope or doped or doping or impurity or		
		dopant)).ti,ab,clm.) and (tft or (thin near film		
		near transistor)).ab.) and (display or		
		displaying or displayed).ti,ab,clm.) and		1
		(c nductiv or conducting or conduct r or		
	<u> </u>	lay r rm tal).ti,ab,clm.		L

1 (((((((pix l.ti,ab,clm. and (tft r (thin n ar	USPAT;	2003/01/31
film near transist r)).ti,ab,clm.) and (driv r	US-PGPUB;	13:54
or driv).ti,ab,clm.) and (gate and	EPO; JPO;	
el ctrod).ti,ab,clm.) and	DERWENT;	
(channel).ti,ab,clm.) and (s urc and drain	IBM_TDB	
and (dop or d ped or doping r impurity or		
dopant)).ti,ab,clm.) and (tft or (thin near film		
near transistor)).ab.) and (display or		
displaying or displayed).ti,ab,clm.) and		
(conductive or conducting or conductor or		
layer or metal).ti,ab,clm.) and		
(substrate.ti,ab,clm.)		

•	197	(US-6480179-\$ or US-6476788-\$ or	USPAT;	2003/01/31
		US-6365917-\$ r US-6335716-\$ r	US-PGPUB;	13:54
		US-6323515-\$ r US-6278131-\$ r	EPO; JP ;]
		US-6271818-\$ or US-6236063-\$ or	DERWENT	
		US-6147667-\$ r US-6146930-\$ r		
		US-6137219-\$ r US-5767930-\$ r		
		US-6498369-\$ or US-6490021-\$ or		
		US-6461899-\$ or US-6246454-\$ or		
		US-5923997-\$ or US-6509939-\$ or		
		US-6500702-\$ or US-6495858-\$ or		
		US-6493046-\$ or US-6417896-\$ or		
		US-6400424-\$ or US-6377322-\$ or		
		US-6356318-\$ or US-6351010-\$).did. or		
		(US-6346730-\$ or US-6307322-\$ or		
		US-6292237-\$ or US-6281957-\$ or		
		US-6281552-\$ or US-6259117-\$ or		
		US-6243146-\$ or US-6194837-\$ or		
		US-6175394-\$ or US-6118506-\$ or		
		US-6057896-\$ or US-6023074-\$ or		
		US-6011274-\$ or US-5990998-\$ or		
		US-5966190-\$ or US-5966189-\$ or		
		US-5940151-\$ or US-5923310-\$ or		<u> </u>
				1
		US-5920362-\$ or US-5920084-\$ or		
		US-5920082-\$ or US-5914762-\$ or		
		US-5856858-\$ or US-5822026-\$ or		
		US-5815226-\$ or US-5796448-\$ or		
		US-5784131-\$).did. or (US-5777700-\$ or		
		US-5763899-\$ or US-5760854-\$ or		
		US-5729308-\$ or US-5724107-\$ or		
		US-5714770-\$ or US-5694185-\$ or		
		US-5686976-\$ or US-5671027-\$ or		
		US-5650636-\$ or US-5641974-\$ or		
		US-5610738-\$ or US-5610736-\$ or		
		US-5546205-\$ or US-5526014-\$ or		
		US-5519521-\$ or US-5459596-\$ or		
		US-5402254-\$ or US-5235448-\$ or		
		US-5159476-\$ or US-5132820-\$ or		
		US-6504215-\$ or US-6486497-\$ or		
		US-6465268-\$ or US-6399933-\$ or		
		US-6380687-\$ or US-6346978-\$).did. or		
		(US-6300174-\$ or US-6288412-\$ or		
		US-6177301-\$ or US-6150692-\$ or		
		US-6136632-\$ or US-5969377-\$ or		
		US-5877514-\$ or US-5811837-\$ or		
		US-5798744-\$ or US-5789763-\$ or		
		US-5764320-\$ or US-5742075-\$ or		
		US-5707882-\$ or US-5656826-\$ or		
		US-5510807-\$ or US-5504348-\$ or		
		US-5426447-\$ r US-5313222-\$ r		
		US-5250931-\$ or US-4644338-\$ r		
		US-6501096-\$ or US-5589406-\$ r		
		US-6496240-\$ or US-6448718-\$ or		
		US-6433852-\$ r US-6411273-\$ r		
		US-6407508-\$).did. or (US-6346718-\$ r		
arab U'-	2/40/	34 9.6 32469996 op 496-6307528-\$ r		
		e U695197505_\$aee N&6166711-\$ r		
MLL2/ S	işt/workspac	US-6157429-\$ r US-6156450-\$ or		†

•	51	((US-6480179-\$ r US-6476788-\$ r	USPAT;	2003/01/31
		US-6365917-\$ r US-6335716-\$ r	US-PGPUB;	13:55
		US-6323515-\$ or US-6278131-\$ r	EPO; JPO;	!
		US-6271818-\$ r US-6236063-\$ r	DERWENT;	
		US-6147667-\$ or US-6146930-\$ or	IBM_TDB	
		US-6137219-\$ or US-5767930-\$ or		
		US-6498369-\$ or US-6490021-\$ or		
		US-6461899-\$ or US-6246454-\$ or		
		US-5923997-\$ or US-6509939-\$ or		
		US-6500702-\$ or US-6495858-\$ or		
		US-6493046-\$ or US-6417896-\$ or		1
		US-6400424-\$ or US-6377322-\$ or		1
		US-6356318-\$ or US-6351010-\$).did. or		
		(US-6346730-\$ or US-6307322-\$ or		
		US-6292237-\$ or US-6281957-\$ or		
		US-6281552-\$ or US-6259117-\$ or		
	1	US-6243146-\$ or US-6194837-\$ or		
		US-6175394-\$ or US-6118506-\$ or		
		US-6057896-\$ or US-6023074-\$ or		
		US-6011274-\$ or US-5990998-\$ or		
		US-5966190-\$ or US-5966189-\$ or		
		US-5940151-\$ or US-5923310-\$ or		
		US-5920362-\$ or US-5920084-\$ or		
		US-5920082-\$ or US-5914762-\$ or		-
		US-5856858-\$ or US-5822026-\$ or		
		US-5815226-\$ or US-5796448-\$ or		
	1	US-5784131-\$).did. or (US-5777700-\$ or		
		US-5763899-\$ or US-5760854-\$ or		
		US-5729308-\$ or US-5724107-\$ or		
		US-5714770-\$ or US-5694185-\$ or		
		US-5686976-\$ or US-5671027-\$ or		
		US-5650636-\$ or US-5641974-\$ or		
		US-5610738-\$ or US-5610736-\$ or		
		US-5546205-\$ or US-5526014-\$ or		
		US-5519521-\$ or US-5459596-\$ or		}
		US-5402254-\$ or US-5235448-\$ or		
		US-5159476-\$ or US-5132820-\$ or		
		US-6504215-\$ or US-6486497-\$ or		1
		US-6465268-\$ or US-6399933-\$ or		
		US-6380687-\$ or US-6346978-\$).did. or		
		(US-6300174-\$ or US-6288412-\$ or		1
		US-6177301-\$ or US-6150692-\$ or		1
		US-6136632-\$ or US-5969377-\$ or		
		US-5877514-\$ or US-5811837-\$ or		-
	1	US-5798744-\$ or US-5789763-\$ or		
		US-5764320-\$ or US-5742075-\$ or		•
		US-5707882-\$ or US-5656826-\$ or		
		US-5510807-\$ or US-5504348-\$ or		
		US-5426447-\$ or US-5313222-\$ r		
		US-5250931-\$ r US-4644338-\$ r		
		US-6501096-\$ or US-5589406-\$ r		
		US-6496240-\$ r US-6448718-\$ r		
		US-6433852-\$ r US-6411273-\$ or		
		US-6407508-\$).did. or (US-6346718-\$ r		
	_	349.63289986 op.15-6307528-\$ r		
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-	54	((pixel and TFT and display and (drive r	USPAT;	2003/02/03
		driver) and substrate and gat and el ctr d	US-PGPUB;	15:08
		and (channel or (chann I near f rming) r	EPO; JPO;	
		channel-forming) and (c nducting r	DERWENT;	
		c nduct or conductiv or metal or	IBM_TDB	
		lay r))).ti,ab,clm. and (capacitor or capacitance)		
	34	(((pixel and TFT and display and (drive or	USPAT;	2003/02/03
		driver) and substrate and gate and electrode	US-PGPUB;	14:53
	1	and (channel or (channel near forming) or	EPO; JPO;	
		channel-forming) and (conducting or	DERWENT;	
]	conduct or conductive or metal or	IBM_TDB	İ
		layer))).ti,ab,clm. and (capacitor or		
		capacitance)) and (dope or doping or doped		
		or dopant or impurity).ti,ab,clm.		
	21	((((pixel and TFT and display and (drive or	USPAT;	2003/02/03
		driver) and substrate and gate and electrode	US-PGPUB;	14:53
		and (channel or (channel near forming) or	EPO; JPO;	
		channel-forming) and (conducting or	DERWENT;	j
		conduct or conductive or metal or	IBM_TDB	
		layer))).ti,ab,clm. and (capacitor or		
		capacitance)) and (dope or doping or doped		
		or dopant or impurity).ti,ab,clm.) and		
		(conduct or conducting or conductive or		1
		metal).ti,ab,clm.		

L	Hits	S arch T xt	DB	Tim stamp
Number	22	(((pixel and TFT and display and (driv or driver) and substrate and gat and lectr de	USPAT; US-PGPUB;	2003/02/03 15:17
		and (chann I or (chann I near forming) r	EPO; JPO;	
		chann I-f rming) and (c nducting r	DERWENT;	1
		c nduct r c nductive or m tal or	IBM_TDB	
		layer))).ti,ab,clm. and (capacitor or	_	
		capacitance)) and (nitrogen or tantalum or		
		titanium or tungsten or ta or ti or mo or		
		molybdenum or al or cu or aluminum or		
		copper).cim.		
	22	((((pixel and TFT and display and (drive or	USPAT;	2003/02/03
		driver) and substrate and gate and electrode	US-PGPUB;	15:12
		and (channel or (channel near forming) or	EPO; JPO;	
		channel-forming) and (conducting or	DERWENT;	-
		conduct or conductive or metal or	IBM_TDB	
		layer))).ti,ab,clm. and (capacitor or	_	
		capacitance)) and (nitrogen or tantalum or		
		titanium or tungsten or ta or ti or mo or		
		molybdenum or al or cu or aluminum or		
		copper).clm.) and substrate.ti,ab,clm.		
_	22	(((((pixel and TFT and display and (drive or	USPAT;	2003/02/03
		driver) and substrate and gate and electrode	US-PGPUB;	15:12
		and (channel or (channel near forming) or	EPO; JPO;	
		channel-forming) and (conducting or	DERWENT;	
		conduct or conductive or metal or	IBM_TDB	
		layer))).ti,ab,clm. and (capacitor or		
		capacitance)) and (nitrogen or tantalum or		
		titanium or tungsten or ta or ti or mo or		
1		molybdenum or al or cu or aluminum or		
		copper).clm.) and substrate.ti,ab,clm.) and		
		(drive or driver).ti,ab,clm.		
-	20	((((((pixel and TFT and display and (drive or	USPAT;	2003/02/03
		driver) and substrate and gate and electrode	US-PGPUB;	15:14
		and (channel or (channel near forming) or	EPO; JPO;	
		channel-forming) and (conducting or	DERWENT;	
		conduct or conductive or metal or	IBM_TDB	
		layer))).ti,ab,clm. and (capacitor or		
		capacitance)) and (nitrogen or tantalum or		
		titanium or tungsten or ta or ti or mo or		
		molybdenum or al or cu or aluminum or		
		copper).clm.) and substrate.ti,ab,clm.) and		
		(drive or driver).ti,ab,clm.) and ((drive or		
		driver) same (tft or (thin near film near		
		transistor))).ti,ab,clm.		

-	18	(((((((pixel and TFT and display and (drive r	USPAT;	2003/02/03
		driv r) and substrate and gate and el ctrode	US-PGPUB;	15:21
		and (channel r (channel near f rming) r	EPO; JPO;	
		chann I-f rming) and (c nducting r	DERWENT;	
		c nduct or conductive r metal r	IBM_TDB	
		lay r))).ti,ab,clm. and (capacitor r		
		capacitance)) and (nitr gen r tantalum r		
		titanium or tungsten or ta or ti or mo or		
		molybdenum or al or cu or aluminum or		
		copper).clm.) and substrate.ti,ab,clm.) and		
		(drive or driver).ti,ab,clm.) and ((drive or		
		driver) same (tft or (thin near film near		
	1	transistor))).ti,ab,clm.) and (pixel same (tft		
		or (thin near film near transistor))).ti,ab,clm.		
_	18	((((((((pixel and TFT and display and (drive or	USPAT;	2003/02/03
-		driver) and substrate and gate and electrode	US-PGPUB;	15:14
		,	•	13.14
		and (channel or (channel near forming) or	EPO; JPO; DERWENT;	
		channel-forming) and (conducting or	,	
		conduct or conductive or metal or	IBM_TDB	
		layer))).ti,ab,clm. and (capacitor or		
	:	capacitance)) and (nitrogen or tantalum or		
		titanium or tungsten or ta or ti or mo or		
		molybdenum or al or cu or aluminum or		
		copper).clm.) and substrate.ti,ab,clm.) and		
		(drive or driver).ti,ab,clm.) and ((drive or		
		driver) same (tft or (thin near film near		
		transistor))).ti,ab,clm.) and (pixel same (tft		
		or (thin near film near		
		transistor))).ti,ab,clm.) and ((drive or driver)		
		near20 (tft or (thin near film near		, [
	j	transistor))).ti,ab,clm.		
-	18	((((((((pixel and TFT and display and (drive	USPAT;	2003/02/03
		or driver) and substrate and gate and	US-PGPUB;	15:20
		electrode and (channel or (channel near	EPO; JPO;	
		forming) or channel-forming) and	DERWENT;	
		(conducting or conduct or conductive or	IBM_TDB	<u> </u>
		metal or layer))).ti,ab,clm. and (capacitor or		
		capacitance)) and (nitrogen or tantalum or		
		titanium or tungsten or ta or ti or mo or		
		molybdenum or al or cu or aluminum or		
		copper).clm.) and substrate.ti,ab,clm.) and		
		(drive or driver).ti,ab,clm.) and ((drive or		
•		driver) same (tft or (thin near film near		
		transistor))).ti,ab,clm.) and (pixel same (tft		
		or (thin near film near		<u> </u>
		transistor))).ti,ab,clm.) and ((drive or driver)		
	1	near20 (tft or (thin near film near		
		1 .		
		transistor))).ti,ab,clm.) and ((drive or driver)		
		n ar10 (tft r (thin near film n ar		
	1	transist r))).ti,ab,clm.		1

•	18	((((((((pixel and TFT and display and (drive	USPAT;	2003/02/03
		or driver) and substrat and gate and	US-P PUB;	15:14
		el tr de and (channel or (chann i near	EPO; JPO;	
		forming) r chann l-f rming) and	DERWENT;	
		(c nducting or conduct or c nductive r	IBM_TDB	
		` -	IBW_IDB	
		m tal r lay r))).ti,ab,clm. and (capacitor or		
		capacitanc)) and (nitrogen r tantalum or		
		titanium or tungsten or ta or ti or mo or		
		molybdenum or al or cu or aluminum or		1 1
		copper).clm.) and substrate.ti,ab,clm.) and		
		(drive or driver).ti,ab,clm.) and ((drive or		
		driver) same (tft or (thin near film near		
		transistor))).ti,ab,clm.) and (pixel same (tft		
		or (thin near film near		
		transistor))).ti,ab,clm.) and ((drive or driver)		
		near20 (tft or (thin near film near		
		transistor))).ti,ab,clm.) and ((drive or driver)		
		near10 (tft or (thin near film near		
		•		
		transistor))).ti,ab,clm.) and ((drive or driver)		
•	, , ,	near100 (tft or (thin near film near	1 	1
		transistor))).ti,ab,clm.		
-	18	(((((((((pixel and TFT and display and (drive	USPAT;	2003/02/03
	1	or driver) and substrate and gate and	US-PGPUB;	15:14
		electrode and (channel or (channel near	EPO; JPO;	
		forming) or channel-forming) and	DERWENT;	
		(conducting or conduct or conductive or	IBM_TDB	
		metal or layer))).ti,ab,clm. and (capacitor or		
		capacitance)) and (nitrogen or tantalum or		
		titanium or tungsten or ta or ti or mo or		
		molybdenum or al or cu or aluminum or		
		copper).clm.) and substrate.ti,ab,clm.) and		
		(drive or driver).ti,ab,clm.) and ((drive or		
		driver) same (tft or (thin near film near		
		· · · · · · · · · · · · · · · · · · ·		
		transistor))).ti,ab,clm.) and (pixel same (tft		
		or (thin near film near		
	ļ	transistor))).ti,ab,clm.) and ((drive or driver)	1	
l I		near20 (tft or (thin near film near	i I	
		transistor))).ti,ab,clm.) and ((drive or driver)		
		near10 (tft or (thin near film near		
		transistor))).ti,ab,clm.) and ((drive or driver)		
		near10 (tft or (thin near film near		
		transistor))).ti,ab,clm.		
-	53	(((pixel and TFT and display and (drive or	USPAT;	2003/02/03
		driver) and substrate and gate and electrode	US-PGPUB;	15:19
		and (channel or (channel near forming) or	EPO; JPO;	
		channel-forming) and (conducting or	DERWENT;	
	1	conduct or conductive or metal or	IBM_TDB	
	!	layer))).ti,ab,clm. and (capacitor or		
		capacitance)) and (nitrogen r tantalum or		
	1	titanium r tungst n r ta or ti or mo or		
		molybd num rai or cu or aluminum r		
		_		
	1	copp r)	1	

	53	((((pixel and TFT and display and (drive or	USPAT;	2003/02/03
-	33		US-P PUB;	
i	1	driver) and substrat and gat and I ctr de		15:20
	İ	and (channel or (chann I near f rming) or	EP ; JPO;	
		chann I-f rming) and (conducting r	DERWENT;	
		c nduct r conductiv r m tal or	IBM_TDB	
		lay r))).ti,ab,clm. and (capacit r or		
		capacitance)) and (nitr gen or tantalum or		
		titanium or tungsten or ta or ti or mo or		
		molybdenum or al or cu or aluminum or		
		copper)) and ((drive or driver) near10 (tft or		
		(thin near film near transistor)))		
_	46	(((((pixel and TFT and display and (drive or	USPAT;	2003/02/03
_		driver) and substrate and gate and electrode	US-PGPUB;	15:24
		and (channel or (channel near forming) or	EPO; JPO;	13.24
			1 '	
		channel-forming) and (conducting or	DERWENT;	
		conduct or conductive or metal or	IBM_TDB	
		layer))).ti,ab,clm. and (capacitor or		
		capacitance)) and (nitrogen or tantalum or		
! 		titanium or tungsten or ta or ti or mo or		
		molybdenum or al or cu or aluminum or		
		copper)) and ((drive or driver) near10 (tft or		
		(thin near film near transistor)))) and (pixel		
		near10 (tft or (thin near film near	<u> </u>	
		transistor))).ti,ab,clm.		
_	36	((((((pixel and TFT and display and (drive or	USPAT;	2003/02/03
		driver) and substrate and gate and electrode	US-PGPUB;	15:25
		and (channel or (channel near forming) or	EPO; JPO;	10.20
		channel-forming) and (conducting or	DERWENT;	
			1	
		conduct or conductive or metal or	IBM_TDB	
		layer))).ti,ab,clm. and (capacitor or		
		capacitance)) and (nitrogen or tantalum or		
		titanium or tungsten or ta or ti or mo or		
		molybdenum or al or cu or aluminum or		
		copper)) and ((drive or driver) near10 (tft or		
		(thin near film near transistor)))) and (pixel		
! 		near10 (tft or (thin near film near		
		transistor))).ti,ab,clm.) and (pixel same		
		(display or displaying) same (driver or drive)		

	20	////nivel and TET and display and (drive an	HEDAT.	2002/02/02
-	30	((((((pixel and TFT and display and (driv or	USPAT; US-PGPUB;	2003/02/03
		driver) and substrate and gate and lectrode	•	15:28
		and (chann r (channel near forming) r	EPO; JPO;	
		channel-forming) and (conducting r	DERWENT;	i
		conduct or c nductive r metal r	IBM_TDB	
		lay r))).ti,ab,clm. and (capacitor or		
		capacitanc)) and (nitrog n r tantalum or	:	
	İ	titanium or tungsten or ta or ti or mo or		
		molybdenum or al or cu or aluminum or		į
		copper)) and ((drive or driver) near10 (tft or		
		(thin near film near transistor)))) and (pixel		ļ
		near10 (tft or (thin near film near		1
		transistor))).ti,ab,clm.) and (pixel same		
]	(display or displaying) same (driver or drive)		
		same substrate same (tft or (thin near film		
		near transistor)))		
	15	((((((pixel and TFT and display and (drive or	USPAT;	2003/02/03
		driver) and substrate and gate and electrode	US-PGPUB;	15:30
		and (channel or (channel near forming) or	EPO; JPO;	
		channel-forming) and (conducting or	DERWENT;	
		conduct or conductive or metal or	IBM TDB	
		layer))).ti,ab,clm. and (capacitor or	15111_155	
		capacitance)) and (nitrogen or tantalum or		
		, , ,		
		titanium or tungsten or ta or ti or mo or		i
		molybdenum or al or cu or aluminum or		
		copper)) and ((drive or driver) near10 (tft or		İ
		(thin near film near transistor)))) and (pixel		
		near10 (tft or (thin near film near		
		transistor))).ti,ab,clm.) and (pixel near20		
		(display or displaying) near20 (driver or		
	1	drive) near20 substrate near20 (tft or (thin		
		near film near transistor)))		1
-	13	((((((pixel and TFT and display and (drive or	USPAT;	2003/02/03
	!	driver) and substrate and gate and electrode	US-PGPUB;	15:29
	ļ -	and (channel or (channel near forming) or	EPO; JPO;	
		channel-forming) and (conducting or	DERWENT;	
		conduct or conductive or metal or	IBM_TDB	
		layer))).ti,ab,clm. and (capacitor or		
		capacitance)) and (nitrogen or tantalum or		
	[titanium or tungsten or ta or ti or mo or		'
		molybdenum or al or cu or aluminum or		I
		copper)) and ((drive or driver) near10 (tft or		
		(thin near film near transistor)))) and (pixel		
		near10 (tft or (thin near film near		
		transistor))).ti,ab,clm.) and (pixel same		
		(display or displaying) same (driver or drive)		
1	j	same substrate same (tft or (thin near film		
		near transistor))).ti,ab,clm.		1
	93	(pix near20 (display or displaying) n ar20	USPAT;	2003/02/03
1	93		US-PGPUB;	15:32
		(driv r or driv) n ar20 substrat near20 (tft	1	17.72
		r (thin n ar film n ar transistor))).ti,ab,clm.	EPO; JPO;	
1			DERWENT;	
	<u> </u>		IBM_TDB	

•	8	((pix I n ar20 (display or displaying) n ar20	USPAT;	2003/02/03
	ŀ	(driver r drive) n ar20 substrate n ar20 (tft	US-PGPUB;	15:34
		or (thin n ar film near	EPO; JPO;	
		transist r))).ti,ab,clm.) and (gate and s urce	DERWENT;	
		and drain and channel).ti,ab,clm.	IBM_TDB	1
	2	((pix I n ar20 (display or displaying) n ar20	USPAT;	2003/02/03
		(driv r r driv) near20 substrat n ar20 (tft	US-P PUB;	15:35
		or (thin near film near	EPO; JPO;	
		transistor))).ti,ab,clm.) and (tantalum or	DERWENT;	
		tungsten or titanium or	IBM_TDB	
	<u> </u>	molybdenum).ti,ab,clm.		
	14	((pixel near20 (display or displaying) near20	USPAT;	2003/02/03
		(driver or drive) near20 substrate near20 (tft	US-PGPUB;	15:38
		or (thin near film near	EPO; JPO;	i
		transistor))).ti,ab,clm.) and (tantalum or	DERWENT;	
]	tungsten or titanium or molybdenum)	IBM_TDB	

L	Hits	S arch T xt	DB	Time stamp
Numb r	631	(tantalum r titanium r tungsten r	USPAT;	2003/02/04
i		m lybd num rta rti orm).clm. and (tft	US-PGPUB;	13:32
		r (thin n ar film n ar transist r)).ab.	EPO; JPO;	
		, ,	DERWENT;	
			IBM_TDB	
	539	((tantalum or titanium or tungsten or	USPAT;	2003/02/04
		molybdenum or ta or ti or mo).clm. and (tft	US-PGPUB;	13:32
		or (thin near film near transistor)).ab.) and	EPO; JPO;	
		substrate.clm.	DERWENT;	1
İ			IBM_TDB	
-	471	(((tantalum or titanium or tungsten or	USPAT;	2003/02/04
1		molybdenum or ta or ti or mo).clm. and (tft	US-PGPUB;	13:32
		or (thin near film near transistor)).ab.) and	EPO; JPO;	
		substrate.clm.) and (tft or (thin near film	DERWENT;	
		near transistor)).clm.	IBM_TDB	İ
	52	((((tantalum or titanium or tungsten or	USPAT;	2003/02/04
		molybdenum or ta or ti or mo).clm. and (tft	US-PGPUB;	13:32
		or (thin near film near transistor)).ab.) and	EPO; JPO;	
		substrate.clm.) and (tft or (thin near film	DERWENT;	
		near transistor)).clm.) and (drive or	IBM_TDB	
		driver).clm.	_	
-	33	(((((tantalum or titanium or tungsten or	USPAT;	2003/02/04
		molybdenum or ta or ti or mo).clm. and (tft	US-PGPUB;	13:33
		or (thin near film near transistor)).ab.) and	EPO; JPO;	
		substrate.clm.) and (tft or (thin near film	DERWENT;	
		near transistor)).clm.) and (drive or	IBM_TDB	
		driver).clm.) and (nitrogen or N or argon or	_	
		Ar or hydrogen or H).clm.		
	25	((((((tantalum or titanium or tungsten or	USPAT;	2003/02/04
		molybdenum or ta or ti or mo).clm. and (tft	US-PGPUB;	13:34
		or (thin near film near transistor)).ab.) and	EPO; JPO;	
		substrate.clm.) and (tft or (thin near film	DERWENT;	İ
		near transistor)).clm.) and (drive or	IBM_TDB	
		driver).clm.) and (nitrogen or N or argon or		İ
		Ar or hydrogen or H).clm.) and (display or		
		pixel).clm.		
	17	(((((((tantalum or titanium or tungsten or	USPAT;	2003/02/04
	• • •	molybdenum or ta or ti or mo).clm. and (tft	US-PGPUB;	13:34
		or (thin near film near transistor)).ab.) and	EPO; JPO;	
		substrate.clm.) and (tft or (thin near film	DERWENT;	
		near transistor)).clm.) and (drive or	IBM_TDB	
		driver).clm.) and (urive or driver).clm.) and (urive or	15.11_156	
		Ar or hydrogen or H).clm.) and (display or		
		pixel).clm.) and (aluminum or al or copper or		
		cu).clm.		Į.

•	14	(((((((tantalum r titanium r tungsten r	USPAT;	2003/02/04
		m lybd num or ta or ti r mo).clm. and (tft	US-P PUB;	13:36
		or (thin n ar film n ar transistor)).ab.) and	EPO; JPO;	
		substrat .clm.) and (tft r (thin near film	DERWENT;	
		n ar transist r)).clm.) and (driv r	IBM_TDB	
		driv r).clm.) and (nitrogen or N or argon or		
		Ar or hydrog n or H).clm.) and (display r		
		pixel).clm.) and (aluminum or al or copper or		
		cu).clm.) and ((drive or driver) same (display		
		or pixel) same substrate).clm.		
•	12	(((((((tantalum or titanium or tungsten or	USPAT;	2003/02/04
		molybdenum or ta or ti or mo).clm. and (tft	US-PGPUB;	13:40
		or (thin near film near transistor)).ab.) and	EPO; JPO;	
		substrate.clm.) and (tft or (thin near film	DERWENT;	
		near transistor)).clm.) and (drive or	IBM_TDB	
		driver).clm.) and (nitrogen or N or argon or		
	į	Ar or hydrogen or H).clm.) and (display or		1
]	pixel).clm.) and (aluminum or al or copper or		
		cu).clm.) and ((drive or driver) near10		
		(display or pixel) near10 substrate).clm.		
_	5	(((((((((tantalum or titanium or tungsten or	USPAT;	2003/02/04
-	3	molybdenum or ta or ti or mo).clm. and (tft	US-PGPUB;	13:38
		or (thin near film near transistor)).ab.) and	EPO; JPO;	10100
		•	1	
		substrate.clm.) and (tft or (thin near film	DERWENT;	
		near transistor)).clm.) and (drive or	IBM_TDB	
		driver).clm.) and (nitrogen or N or argon or		
		Ar or hydrogen or H).clm.) and (display or		•
		pixel).clm.) and (aluminum or al or copper or		
		cu).clm.) and ((drive or driver) near10		
		(display or pixel) near10 substrate).clm.)		
		and (conductor or conducting or conducter		
	_ 1	or conductor or conductive).clm.		0000/00/0
•	5	(((((((tantalum or titanium or tungsten or	USPAT;	2003/02/04
		molybdenum or ta or ti or mo).clm. and (tft	US-PGPUB;	13:39
		or (thin near film near transistor)).ab.) and	EPO; JPO;	
		substrate.clm.) and (tft or (thin near film	DERWENT;	
		near transistor)).clm.) and (drive or	IBM_TDB	
		driver).clm.) and (nitrogen or N or argon or		
		Ar or hydrogen or H).clm.) and (display or		
		pixel).clm.) and (aluminum or al or copper or		
	1	cu).clm.) and ((drive or driver) near10		
		(display or pixel) near10 substrate).clm.)		
		and (conductor or conducting or conducter		
		or conductor or conductive or conduct).clm.		
-	296	((tantalum or titanium or tungsten or	USPAT;	2003/02/04
		molybdenum or ta or ti or mo).clm. and (tft	US-PGPUB;	13:39
		or (thin near film near transistor)).ab.) and	EPO; JPO;	
		(conductor or conducting or conducter or	DERWENT;	
		c nduct rorc nductive or conduct).clm.	IBM_TDB	İ

-	11	(((tantalum or titanium or tungsten or	USPAT;	2003/02/04
		molybd num or tarti or mo).clm. and (tft	US-PGPUB;	13:44
		or (thin near film n ar transist r)).ab.) and	EPO; JPO;	
		(conductor or c ndu ting or c nduct r or	DERWENT;	
		conduct rorc nductive rconduct).clm.)	IBM_TDB	
	4	and ((drive r driver) near10 (display r		
		pix I) n ar10 substrat).clm.		
•	160	((tft or (thin near film near transistor)) same	USPAT;	2003/02/04
		(pixel) same display same (drive or	US-PGPUB;	13:46
		driver)).clm.	EPO; JPO;	
			DERWENT;	ļ
			IBM_TDB	
	93	(((tft or (thin near film near transistor)) same	USPAT;	2003/02/04
		(pixel) same display same (drive or	US-PGPUB;	13:46
		driver)).clm.) and (gate and electrode).clm.	EPO; JPO;	10.40
		divery.ciii.) and (gate and electrode).ciiii.	DERWENT;	
			1	
	36	(///454 ou (4him magu film magu tugunintau))	IBM_TDB	2003/02/04
•	36	((((tft or (thin near film near transistor))	USPAT;	
		same (pixel) same display same (drive or	US-PGPUB;	13:47
		driver)).clm.) and (gate and electrode).clm.)	EPO; JPO;	
		and channel.cim.	DERWENT;	
			IBM_TDB	
-	32	(((((tft or (thin near film near transistor))	USPAT;	2003/02/04
		same (pixel) same display same (drive or	US-PGPUB;	13:48
		driver)).clm.) and (gate and electrode).clm.)	EPO; JPO;	1
		and channel.clm.) and ((drive or driver)	DERWENT;	
		near10 (pixel or display)).clm.	IBM_TDB	
-	13	(((((tft or (thin near film near transistor))	USPAT;	2003/02/04
		same (pixel) same display same (drive or	US-PGPUB;	13:52
	:	driver)).clm.) and (gate and electrode).clm.)	EPO; JPO;	
		and channel.clm.) and ((drive or driver)	DERWENT;	
		near10 (pixel or display) near10	IBM_TDB	
		substrate).clm.		
-	10	((((((tft or (thin near film near transistor))	USPAT;	2003/02/04
		same (pixel) same display same (drive or	US-PGPUB;	13:52
		driver)).clm.) and (gate and electrode).clm.)	EPO; JPO;	
		and channel.clm.) and ((drive or driver)	DERWENT:	•
		near10 (pixel or display) near10	IBM TDB	
		substrate).clm.) and (tantalum or titanium or	15155	
		tungsten or molybdenum or ta or ti or mo)		
_	8	((((((tft or (thin near film near transistor))	USPAT;	2003/02/04
-		same (pixel) same display same (drive or	US-PGPUB;	13:51
		1	· ·	13.31
		driver)).clm.) and (gate and electrode).clm.)	EPO; JPO;	}
		and channel.clm.) and ((drive or driver)	DERWENT;	
		near10 (pixel or display) near10	IBM_TDB	
		substrate).clm.) and (tantalum or titanium or		1
		tungsten or molybdenum or ta or ti or mo))		
		and (conductor or conduct or conducting or		
	İ	c nductive)		

•	8	(((((tft r (thin n ar film n ar transistor))	USPAT;	2003/02/04
		same (pixel) same display same (driv r	US-PGPUB;	13:54
		driver)).clm.) and (gate and electrod).clm.)	EPO; JPO;	
		and channel.clm.) and ((drive r driver)	DERWENT;	
		n ar5 (pix l r display) near5 substrat).clm.	IBM_TDB	
	7	(((((tft r (thin n ar film near transistor))	USPAT;	2003/02/04
		same (pixel) same display same (drive or	US-PGPUB;	13:52
		driver)).clm.) and (gate and electrode).clm.)	EPO; JPO;	ļ
		and channel.clm.) and ((drive or driver)	DERWENT;	
		near5 (pixel or display) near5	IBM_TDB	
		substrate).clm.) and (tantalum or titanium or		1
		tungsten or molybdenum or ta or ti or mo)		
	13	(((((tft or (thin near film near transistor))	USPAT;	2003/02/04
		same (pixel) same display same (drive or	US-PGPUB;	13:54
		driver)).clm.) and (gate and electrode).clm.)	EPO; JPO;	
		and channel.clm.) and ((drive or driver)	DERWENT;	
		near10 (pixel or display) near10	IBM_TDB	
		substrate).clm.		